



SSC7002EGS6

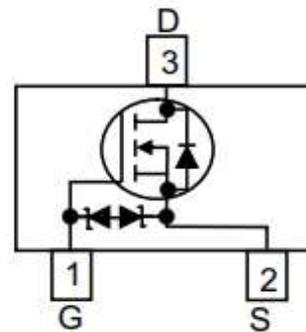
N-Channel Small Switching MOSFET with ESD Protection

➤ **Features**

| VDS | VGS | RDSON Typ. | ID | ESD |
|-----|------|------------|------|-----|
| 60V | ±20V | 2R@10V | 0.3A | 3kV |
| | | 3R@4V5 | | |

➤ **Pin configuration**

Top view

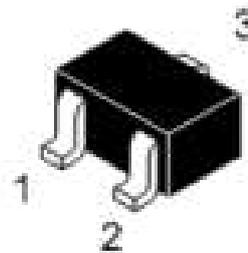


➤ **Description**

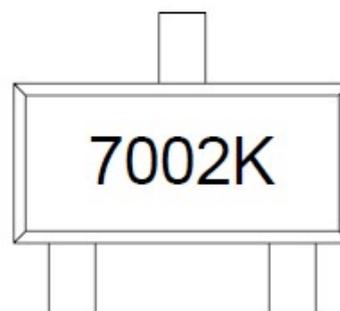
This device is an N-Channel enhancement mode MOSFET, with low on-resistance, fast switching speed and low threshold voltage, it is ideal for portable equipment.

➤ **Applications**

- Direct Logic-Level Interface: TTL/CMOS
- Drivers: Relays, Solenoids, Lamps, Hammers
- Display, Memories, Transistors, etc.
- Battery Operated System
- Solid-State Relays



SOT23



Marking

➤ **Ordering Information**

| Device | Package | Shipping |
|-------------|---------|-----------|
| SSC7002EGS6 | SOT23 | 3000/Reel |



➤ **Absolute Maximum Ratings**($T_A=25^{\circ}\text{C}$ unless otherwise noted)

| Symbol | Parameter | Ratings | Unit |
|-----------|---------------------------------------|------------|--------------------|
| V_{DSS} | Drain-to-Source Voltage | 60 | V |
| V_{GSS} | Gate-to-Source Voltage | ± 20 | V |
| I_D | Continuous Drain Current ^a | 0.3 | A |
| I_{DM} | Pulsed Drain Current ^b | 0.8 | A |
| P_D | Power Dissipation ^c | 0.83 | W |
| P_{DSM} | Power Dissipation ^a | 0.35 | W |
| T_J | Operation junction temperature | -55 to 150 | $^{\circ}\text{C}$ |
| T_{STG} | Storage temperature range | -55 to 150 | $^{\circ}\text{C}$ |

➤ **Thermal Resistance Ratings**($T_A=25^{\circ}\text{C}$ unless otherwise noted)

| Symbol | Parameter | Typical | Maximum | Unit |
|-----------------|---|---------|---------|-----------------------------|
| $R_{\theta JA}$ | Junction-to-Ambient Thermal Resistance ^a | | 357 | $^{\circ}\text{C}/\text{W}$ |
| $R_{\theta JC}$ | Junction-to-Case Thermal Resistance | | 159 | |

Note:

- The value of $R_{\theta JA}$ is measured with the device mounted on 1 in² FR-4 board with 2oz.copper,in a still air environment with $T_A=25^{\circ}\text{C}$.The value in any given application depends on the user is specific board design. The current rating is based on the $t \leq 10\text{s}$ thermal resistance rating.
- Repetitive rating, pulse width limited by junction temperature.
- The power dissipation P_D is based on $T_{J(MAX)}=150^{\circ}\text{C}$, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heat sinking is used.

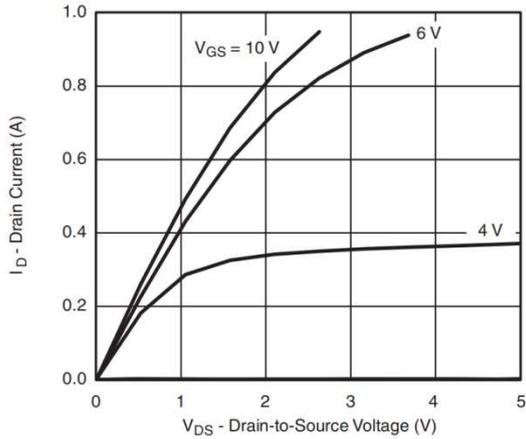


➤ **Electronics Characteristics**($T_A=25^{\circ}\text{C}$ unless otherwise noted)

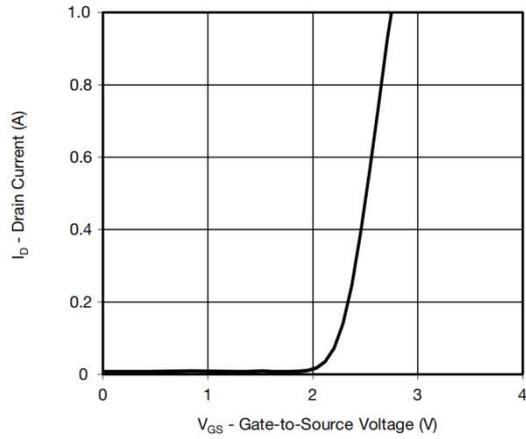
| Symbol | Parameter | Test Conditions | Min | Typ. | Max | Unit |
|---------------|------------------------------------|--|-----|------|----------|---------|
| $V_{(BR)DSS}$ | Drain-Source Breakdown Voltage | $V_{GS}=0V, I_D=10\mu A$ | 60 | | | V |
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{DS}=V_{GS}, I_D=250\mu A$ | 1 | | 2.5 | V |
| $R_{DS(on)}$ | Drain-Source On- Resistance | $V_{GS}=10V, I_D=0.5A$ | | 2 | 6 | R |
| | | $V_{GS}=4.5V, I_D=0.05A$ | | 3 | 8 | |
| I_{DSS} | Zero Gate Voltage Drain Current | $V_{DS}=60V, V_{GS}=0V$ | | | 1 | μA |
| I_{GSS} | Gate-Source leak current | $V_{GS}=\pm 20V, V_{DS}=0V$ | | | ± 10 | μA |
| G_{FS} | Transconductance | $V_{DS}=10V, I_D=0.2A$ | | 0.08 | | S |
| V_{SD} | Forward Voltage | $V_{GS}=0V, I_S=0.2A$ | | 0.7 | 1.3 | V |
| C_{iss} | Input Capacitance | $V_{DS}=25V, V_{GS}=0V,$ $f=1\text{MHz}$ | | 32 | | pF |
| C_{oss} | Output Capacitance | | | 7 | | |
| C_{rss} | Reverse Transfer Capacitance | | | 3 | | |
| $T_{D(ON)}$ | Turn-on delay time | $V_{GS}=10V,$ $V_{DS}=20V, R_G=20R,$ $R_L=60R$ | | 4.2 | | ns |
| T_r | Rise Time | | | 3.8 | | |
| $T_{D(OFF)}$ | Turn-off delay time | | | 22 | | |
| T_f | Fall Time | | | 14 | | |
| Q_G | Total Gate Charge | $V_{GS}=10V, V_{DS}=15V,$ $I_D=0.2A$ | | 0.4 | | nC |
| Q_{GS} | Gate Source Charge | | | 0.1 | | |
| Q_{GD} | Gate Drain Charge | | | 0.11 | | |



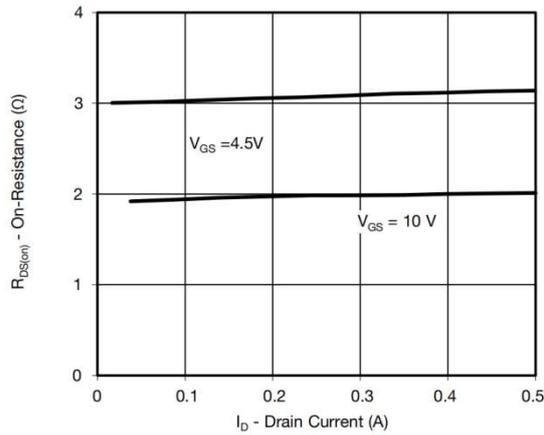
➤ **Typical Characteristics** ($T_A=25^\circ\text{C}$ unless otherwise noted)



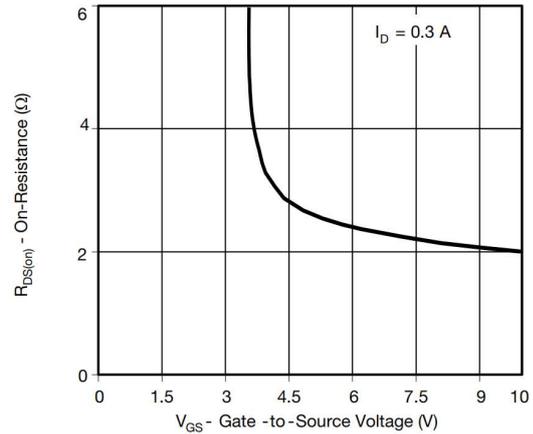
Output Characteristics



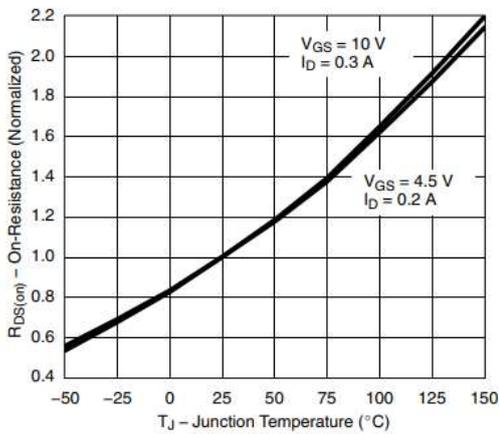
Transfer Characteristics



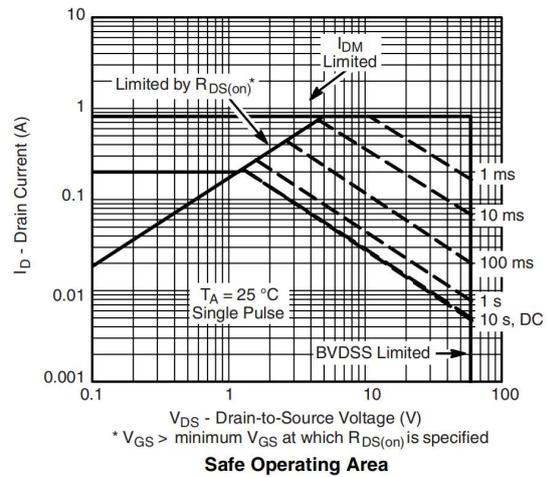
On-Resistance vs. Drain Current



On-Resistance vs. Gate-to-Source Voltage

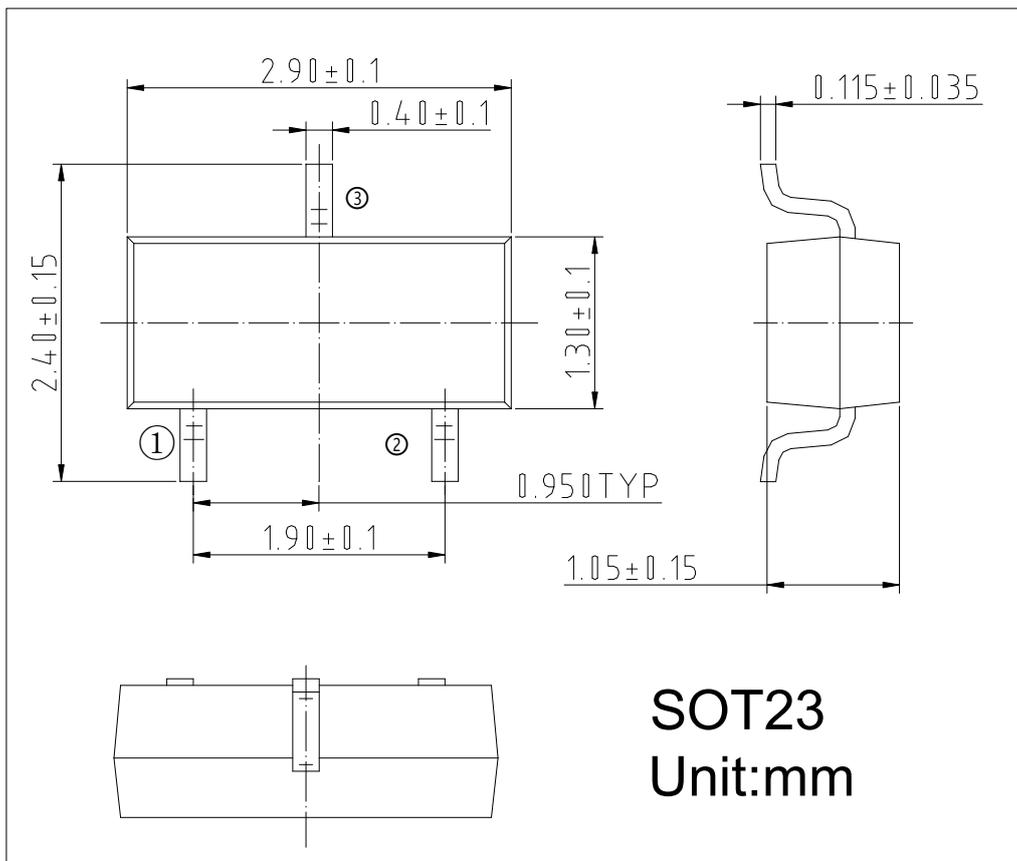


On-Resistance vs. Junction Temperature



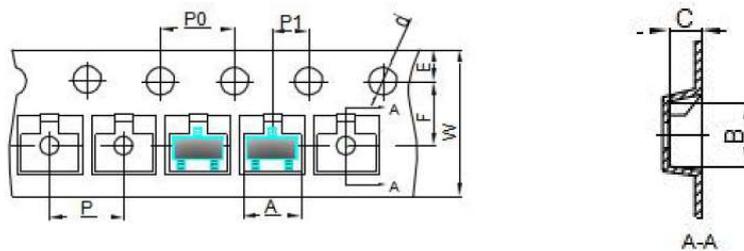
Safe Operating Area

➤ **Package Information**



SOT-23 Tape and reel

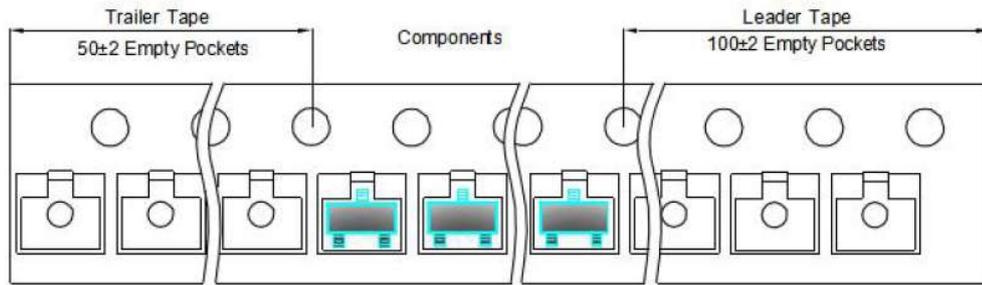
SOT-23 Embossed Carrier Tape



| Dimensions are in millimeter | | | | | | | | | | |
|------------------------------|----------|----------|----------|-------|----------|----------|---------|---------|--------|-------|
| Pkg type | A | B | C | d | E | F | P0 | P | P1 | W |
| SOT-23 | 3.15±0.1 | 2.77±0.1 | 1.22±0.1 | Ø1.50 | 1.75±0.1 | 3.5±0.05 | 4.0±0.1 | 4.0±0.1 | 2±0.05 | 8±0.1 |

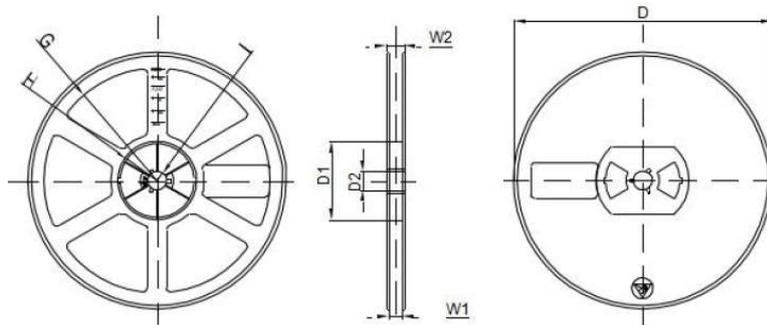


SOT-23 Tape Leader and Trailer



SOT23 带尾(空封 40 格)、带头 (空封 100 格) 空封数

SOT-23 Reel



| Dimensions are in millimeter | | | | | | | | |
|------------------------------|---------|---------|----------|--------|--------|-----------|-------|--------|
| Reel Option | D | D1 | D2 | G | H | I | W1 | W2 |
| 7" Dia | Ø178.00 | Ø54±0.2 | 13.3±0.2 | R79.00 | R26.00 | R6.50±0.2 | 9±0.5 | 12±0.5 |



➤ **History Version**

| | | |
|------|--------------------------|------------|
| V1.0 | Product Release | |
| V2.0 | Update POD and Tape&Reel | 2020-08-28 |
| V3.0 | Update Curve | 2021-08-31 |

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